MN74HC365/MN74HC365S

Hex TRI-STATE Buffers

■ Outline

MN74HC365/MN74HC365S consists of high speed non-inverting buffers having six 3-state outputs.

Because of the large current outputs, these buffers assure high speed operation even when driving a large capacity bus line. The six gates are simultaneously controlled by two 3-state control inputs $(\overline{G1}, \overline{G2})$ to enable the outputs when the level is "L".

Owing to the silicon gate CMOS process, these buffers have realized low power consumption and high noise immunity equivalent to those of a standard CMOS and the operation speed as high as of an LS TTL, and can directly drive fifteen LS TTL inputs.

To protect the input and output against electrostatic breakdown, a resistor and a diode are used for the V_{CC} and the GND. The pin configuration and the function are the same as those of the stanard 54LS/74LS logic family.

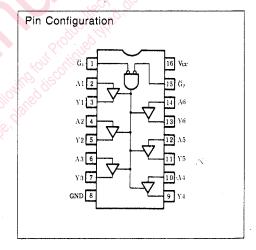
■ Truth Table

	Output			
<u></u> G1	G 2 ◆	A	J.	
Н	×	×	Hi-Z	
×	Н	×	· Hi-Z	
L	· L	Н	Н	
L	L	L	L.////	

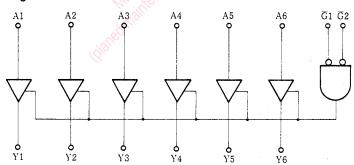
Note 1. Hiz : High impedance

2. × : "H" or "L" either will do.

P-3 16-pin plastic DIL package P-4 16-pin PANAFLAT package (SO-16D)



■ Logic Diagram



■ Absolute Maximum Ratings

Item			Symbol	Rating	Unit
Supply voltage			V _{cc} -	-0.5~+7.0	V
Input output	voltage			$-0.5 \sim V_{CC} + 0.5$	V
Input protective diode current			I_{IK}	±20	mA
Output parasitic diode current			I_{OK}	±20	mA
Output current			I_{O}	±35	mA
Supply current			I _{CC} , I _{GND}	±70	mA
Storage temperature			T _{stg}	−65~+150	°C
Power MN74HC365	Ta=-40~+60°C	P_{D}	400	mW	
	WIN /4HC365	$Ta = +60 \sim +85^{\circ}C$	I ID	Decrease to 200mW at the rate of 8mW/°C	11144
dissipation	MN74HC365S	$Ta = -40 \sim +60^{\circ}C$	D	275	mW
	WIN/4/1C300S	$Ta = +60 \sim +85^{\circ}C$	P_D	Decrease to 200mW at the rate of 3.8mW/°C	111 44

■ Recommended Operating Conditions

Item	Symbol	V _{cc} (V)	Rating	Unit	
Operating power supply voltage	Vcc		1.4~6.0	V	
Input output voltage	V _I , V _O		0~V _{cc}	16. A	
Operating temperature	T _A		-40~+85	°C	
		2.0	0~1000	ns	
Input rise, fall time	t _r , t _f	4.5	0~500	ns	
		6.0	0~400	ns	

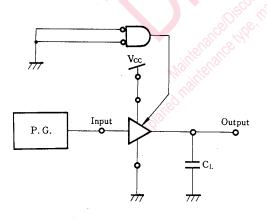
■ DC Characteristics (GND=0V)

Item		37	Test Condition		Temperature						
	Symbol	V _{cc} (V)	Vı	V _o Unit		Ta=25°C			Ta=-40~+85°C		Unit
					Unit	min.	typ.	max.	min.	max.	
-		2.0				1.5			1.5		
Input voltage high level	V _{IH}	4.5				3.15			3.15		V
		6.0			<i>100</i>	4.2			4.2		
		2.0		111	2 12/6			0.3	1.	0.3	
Input voltage low level	VIL	4.5		180				0.9		0.9	v
		6.0		The Fol	Q.			1.2		1.2	
		2.0	:,50	-20.0	μΑ	1.9	2.0		1.9		
		4.5	VIH	-20.0	μ A	4.4	4.5		4.4		
Output voltage high level	V_{OH}	6.0	or	-20.0	μ A	5.9	6.0		5.9		V
		4.5	V_{iL}	-6.0	mA	3.92			3.84		
,	1.	6.0	0.	-7.8	mA	5.48		-	5.34		
		2.0		20.0	μΑ		0.0	0.1		0.1	
	3-	4.5	V_{IH}	20.0	μΑ		0.0	0.1		0.1	
Output voltage low level	Vol	6.0	or	20.0	μ A		0.0	0.1		0.1	V
	18/10	4.5	V_{iL}	6.0	mA			0.26		0.33	
		6.0		7.8	mA			0.26		0.33	
Input leakage current	I_1	6.0	$V_i = V_{Ci}$	or GNI)			±0.1		±1.0	μΑ
3-state output OFF	I _{oz}	6.0		or V_{IL}				±0.5		±5.0	μΑ
leakage current	102		V ₀ =V _{cc} or GND								
Static supply current	I_{cc}	6.0	$V_{i}=V_{co}$	or GNI	$I_0=0$			8.0		80.0	μ A

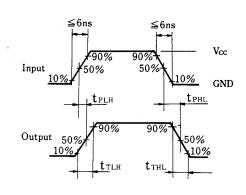
■ AC Characteristics (GND=0V, Input transition time≤6ns, C_L=50pF)

Item		V _{cc} (V)		Temperature					
	Symbol		Test Condition	Ta=25°C			Ta=-40~+85°C		Unit
				min.	typ.	max.	min.	max.	
		2.0			16	75		95	
Output rise time	t _{TLH}	4.5			7	15		19	ns
		6.0			6	13		16	
		2.0			10	75		95	
Output fall time	t _{THL}	4.5			4	15		19	ns
		6.0			3	13		16	
Propagation time		2.0			13	75		95	
	t _{PLH}	4.5			7	15		19	ns
(L→H)		6.0			7	13		16	
D		2.0			11	75		95	
Propagation time	t _{PHL}	4.5			6	15		19	ns
(H→L)		6.0			6	13		16	
3-state propagation time		2.0			20	100		125	
(H→Z)	t _{PHZ}	4.5	$R_L=1k\Omega$		13	20	-	25	ns
$(\Pi \rightarrow L)$		6.0			13	17	₩.	21	
3-state propagation time		2.0			25	125 2	1900 11W	155	
·	t _{PLZ}	4.5	$R_L=1k\Omega$		15	25	collin	31	ns
$(L \rightarrow Z)$		6.0			12	21	1/2	26	
3-state propagation time (Z→H)		2.0			22	100		125	
	t _{PZH}	4.5	$R_L=1k\Omega$		10	20		25	ns
		6.0		3	9	17		21	
3-state propagation time (Z→L)		2.0		100	27	100		125	
	t _{PZL}	4.5	$R_L=1k\Omega$	110 11	12	20		25	ns
		6.0		4.90	10	17		21	

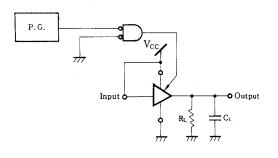
- Switching time measuring circuit and waveforms
- (1) t_{TLH}, t_{THL}, t_{PLH} ,t_{PHL}
- 1. Measuring circuit



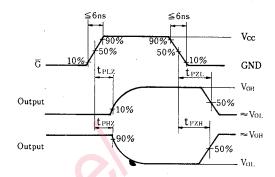
2. Switching waveforms



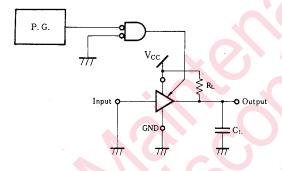
- (2) t_{PHZ}, t_{PZH}
- 1. Measuring circuit



2. Switching waveforms



- (3) t_{PLZ} , t_{PZL}
- 1. Measuring circuit



2. Switching waveforms

See above (2) 2 for waveforms.



Request for your special attention and precautions in using the technical information and semiconductors described in this book

- (1) If any of the products or technical information described in this book is to be exported or provided to non-residents, the laws and regulations of the exporting country, especially, those with regard to security export control, must be observed.
- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products. No license is granted in and to any intellectual property right or other right owned by Panasonic Corporation or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information described in this book.
- (3) The products described in this book are intended to be used for standard applications or general electronic equipment (such as office equipment, communications equipment, measuring instruments and household appliances).
 - Consult our sales staff in advance for information on the following applications:
 - Special applications (such as for airplanes, aerospace, automobiles, traffic control equipment, combustion equipment, life support systems and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
 - · Any applications other than the standard applications intended.
- (4) The products and product specifications described in this book are subject to change without notice for modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most up-to-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.
- (5) When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful not to exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
- Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages, for example, by using the products.
- (6) Comply with the instructions for use in order to prevent breakdown and characteristics change due to external factors (ESD, EOS, thermal stress and mechanical stress) at the time of handling, mounting or at customer's process. When using products for which damp-proof packing is required, satisfy the conditions, such as shelf life and the elapsed time since first opening the packages.
- (7) This book may be not reprinted or reproduced whether wholly or partially, without the prior written permission of our company.

20080805